

Form PTO-1449					Attorney Docket No. <b>062002-1751</b>		Serial No. <b>09/855,972</b>	
<b>INFORMATION DISCLOSURE CITATION</b>					Applicant <b>Martin, et al.</b>			
(Use several sheets if necessary)					Filing Date <b>05/15/2001</b>		Group <b>3742</b>	

U.S. PATENT DOCUMENTS							
Examiner Initials	Item	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
pt ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓	1A	1,712,407	5/7/1929	Skaupy			8/30/1921
	1B	2,037,075	4/14/1936	Haines	250	27.5	10/25/1933
	1C	3,304,456	2/14/1967	De Lany et al.	313	182	3/4/1963
	1D	3,879,597	4/22/1975	Bersin et al.	219	121	8/16/1974
	1E	4,031,424	6/21/1977	Penfold et al.	313	146	3/3/1975
	1F	4,207,158	6/10/1980	Freeman	204	180	5/18/1979
	1G	4,259,145	3/31/1981	Harper et al.	156	643	6/29/1979
	1H	4,298,443	11/3/1981	Maydan	204	192	12/20/1979
	1I	4,309,267	1/5/1982	Boyd et al.	204	298	7/21/1980
	1J	4,450,787	5/29/1984	Weakliem et al.	118	723	5/29/1984
	1K	4,496,881	1/29/1985	Cheever	315	357	9/29/1982
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	1L						
	1M						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
pt ↓ ↓ ↓ ↓	1N	P. Breisacher et al. "Comparative Stabilities of Gaseous Alane, Gallane and Indane" Journal of the American Chemical Society pp. 4255-4258 87:19 Oct 5, 1965.					
	1O	S. Veprek et al. "The Preparation of Thin Layers of Ge and Si by Chemical Hydrogen Plasma Transport." Solid-State Electronics Pergamon Press 1968 vol. 11 pp. 683-684.					
	1P	E. Wiberg et al "Hydrides of the Elements of Main Groups I-IV" New York 1971 Chapter 6 pp. 443-460.					
	1Q	A.P. Webb "Reactivity of Solid Silicon with Hydrogen Under Conditions of a Low Pressure Plasma." Chemical Physics Letters vol 62 No 1 Mar 15, 1979 pp 173-177.					
	1R	S. Veprek et al. "Parameters Controlling the Deposition of Amorphous and Microcrystalline Silicon in Si/H Discharge Plasmas." Journal De Physique (Paris) 42 C4-251 (1981).					
* EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.							
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U.S. PATENT DOCUMENTS							
Examiner Initials	Item	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
pt ↓	2A	4,609,428	9/2/1986	Fujimara	156	643	7/18/1985
	2B	4,871,580	10/3/1989	Schram et al.	427	38	6/13/1988
	2C	4,874,459	10/17/1989	Coldren et al.	156	643	10/17/1988
	2D	5,003,178	3/26/1991	Livesay	250	492.300	11/14/1988
	2E	5,039,376	8/13/1991	Zukotynski et al.	156	643	8/13/1990
	2F	5,138,169	8/11/1992	Yamazaki et al.	250	398	7/26/1991
	2G	5,145,554	9/8/1992	Seki et al.	156	643	2/22/1990
	2H	5,241,535	8/31/1993	Yoshikawa	370	60	9/18/1991
	2I	5,298,896	3/29/1994	Lei et al.	341	51	3/15/1993
	2J	5,309,232	5/3/1994	Hartung et al.	348	384	7/16/1993
	2K	5,331,249	7/19/1994	Minamikata et al.	313	632	12/20/1991
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
	2L						
	2M						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
pt ↓	2N	S. Veprek et al "Electron-Impact-Induced Anisotropic Etching of Silicon by Hydrogen" Plasma Chemistry and Plasma Processing vol. 2 No 3 1982.					
	2O	S. Veprek "Highlights of Preparative Solid State Chemistry in Low Pressure Plasmas." Pure & Appl. Chem. Vol. 54 No. 6 pp. 1197-1220. 1982.					
	2P	J.R. Creighton "Hydrogen Chemisorption and Reaction on GaAs(100)." J. Vac. Sci. Technol. A 8 (6) Nov/Dec 1990 pp. 3984-3987.					
	2Q	H.P. Gillis et al "Low-Energy Electron Beam Enhanced Etching of Si(100)-(2x1) by Molecular Hydrogen" J. Vac. Sci. Technol B. vol. 10 No. 6. Nov/Dec 1992.					
	2R	H. Watanabe et al "Electron-beam-assisted Dry Etching for GaAs using Electron Cyclotron Resonance Plasma Electron Source" Appl Phys. Lett 61 (25) Dec 21, 1992 pp. 3011-3013.					

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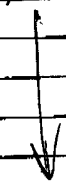
  

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pt ↓	3A	5,352,953	10/4/1994	Wakabayashi et al.	313	631	4/1/1992	
	3B	5,368,676	11/29/1994	Nagaseki et al.	156	345	12/9/1993	
	3C	5,418,423	5/23/1995	Murray	313	589	10/19/1992	
	3D	5,453,305	9/26/1995	Lee	427	562	9/2/1993	
	3E	5,457,298	10/10/1995	Nelson et al.	219	121.52	7/27/1993	
	3F	5,485,210	1/16/1996	Lim et al.	348	409	6/7/1993	
	3G	5,497,053	3/5/1996	Tang et al.	315	366	11/15/1993	
	3H	5,556,501	9/17/1996	Collins et al.	156	345	4/1/1993	
	3I	5,572,088	11/5/1996	Aizawa et al.	313	491	6/1/1995	
	3J	5,606,370	2/25/1997	Moon	348	390	7/11/1995	
	3K	5,631,978	5/20/1997	Galand et al.	382	240	5/11/1992	
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation Yes No	
	3L							
	3M							
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)								
pt ↓	3N	K. Choquette et al "Hydrogen Plasma Processing of GaAs and AlGaAs" J. Vac. Sci. Technol B. vol 11 No. 6 Nov/Dec 1993 pp 2025-2032.						
	3O	H.P. Gillis et al. "Low Energy Electron-Enhanced Etching of Si(100) in Hydrogen/Helium Direct-Current Plasma." Appl. Phys. Lett. 66 (19) May 8, 1995.						
	3P	H.P. Gillis et al. "The Dry Etching of Group III-Nitride Wide-Bandgap Semiconductors" Journal of Materials 48 50-55 (1996).						
	3Q	H.P. Gillis et al "Low Energy Electron-Enhanced Etching of GaAs(100) In a Chlorine/Hydrogen DC Plasma." Appl. Phys. Lett 68(16) Apr. 15, 1996.						
	3R	H.P. Gillis et al "Low Energy Electron-Enhanced Etching of GaN/Si in Hydrogen Direct Current Plasma" J. Electrochem Soc. Vol 143. No. 11 Nov. 1996.						
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<i>pk</i> 	4A	5,660,744	8/26/1997	Sekine et al.	219	121.43	6/19/1995
	4B	5,882,538	3/16/1999	Martin et al.	216	71	8/28/1996
	4C	5,890,102	3/30/1999	Kossentini et al.	702	181	10/24/1996
	4D	5,917,285	6/29/1999	Gillis et al.	313	632	7/23/1997
	4E	6,033,587	3/7/2000	Martin et al.	216	71	12/3/1997
	4F	6,258,287	7/10/2001	Martin et al.	216	71	9/17/1997
	4G						
	4H						
	4I						
	4J						
	4K						

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						Yes No
	4L					
	4M					

OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, etc.)</i>		
<i>pk</i>	4N	H.P. Gillis et al "Highly Anisotropic, Ultra-smooth Patterning of GaN/SiC by Low Energy Electron Enhanced Etching in DC Plasma" J. Electronic Mat 26, 301-305 (1997) pp 1-16.
	4O	
	4P	
	4Q	
	4R	

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